



BSH205G2

20 V, P-channel Trench MOSFET
29 April 2015

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology
- Enhanced power dissipation capability of 890 mW
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|----------------------------------|---|-----|-----|------|------------|
| V_{DS} | drain-source voltage | $T_J = 25\text{ °C}$ | - | - | -20 | V |
| V_{GS} | gate-source voltage | | -8 | - | 8 | V |
| I_D | drain current | $V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$ | [1] | - | -2.3 | A |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = -4.5\text{ V}; I_D = -2\text{ A}; T_J = 25\text{ °C}$ | - | 120 | 170 | m Ω |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

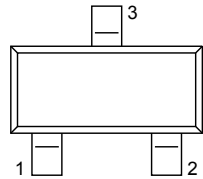
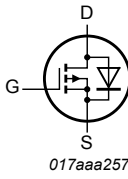


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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|--|
| 1 | G | gate |  <p>TO-236AB (SOT23)</p> |  <p>017aaa257</p> |
| 2 | S | source | | |
| 3 | D | drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|----------|--|---------|
| | Name | Description | Version |
| BSH205G2 | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BSH205G2 | %KB |

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---------------------------|-------------------------|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | -2.3 | A |
| | | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -2 | A |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -1.2 | A |
| I _{DM} | peak drain current | T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs | | - | -8 | A |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 480 | mW |
| | | | [1] | - | 890 | mW |
| | | T _{sp} = 25 °C | | - | 6250 | mW |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain diode | | | | | | |
| I _S | source current | T _{sp} = 25 °C | [1] | - | -0.8 | A |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

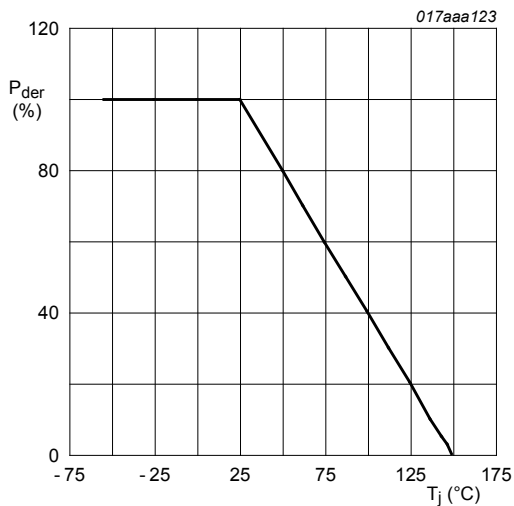


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

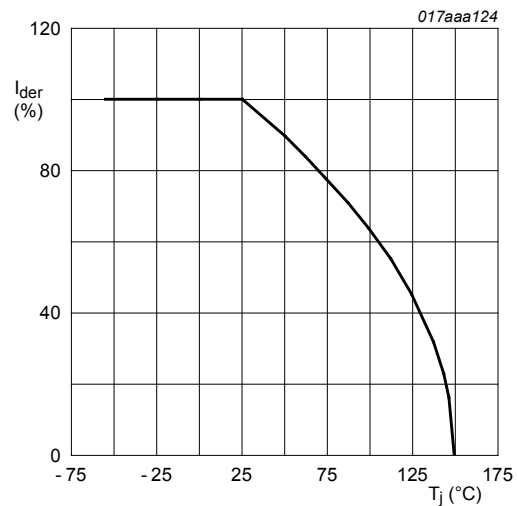
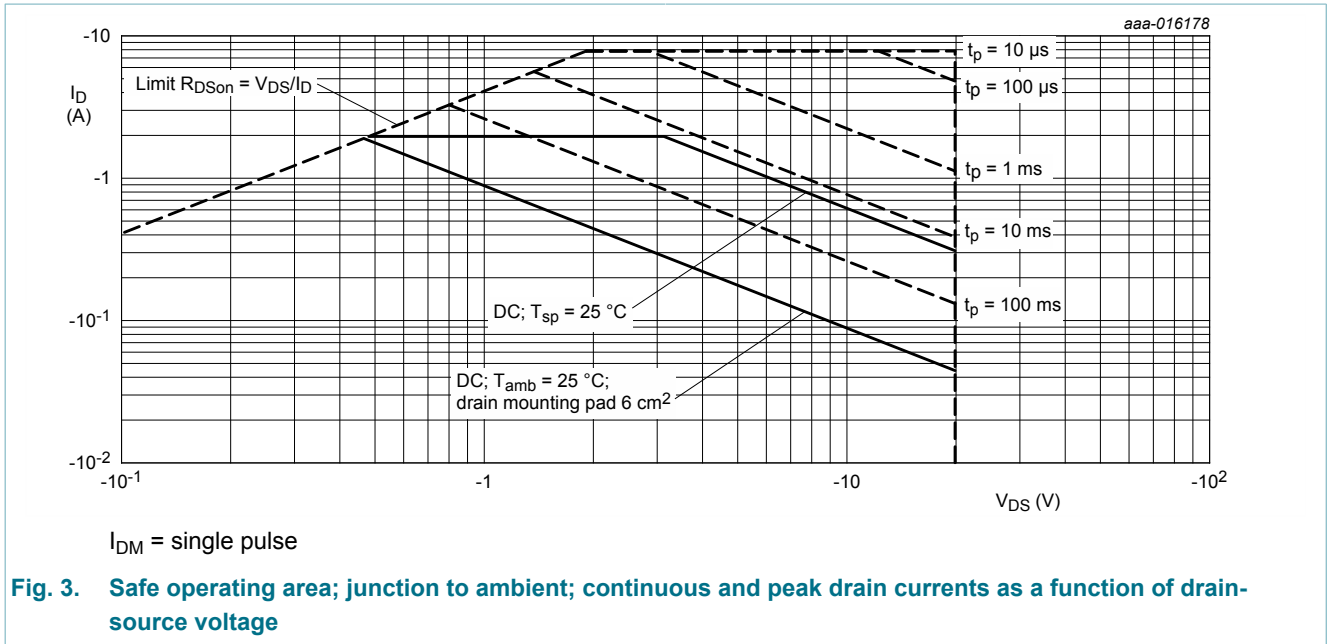


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | [1] | - | 230 | 260 | K/W |
| | | | [2] | - | 120 | 140 | K/W |
| | | in free air; t ≤ 5 s | [2] | - | 85 | 100 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 15 | 20 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

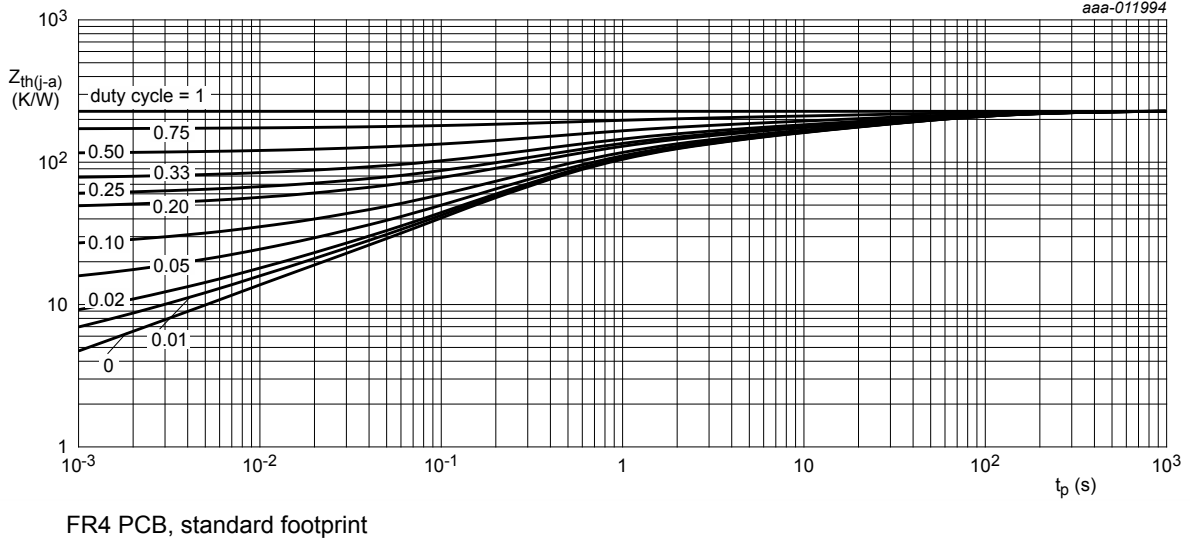


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

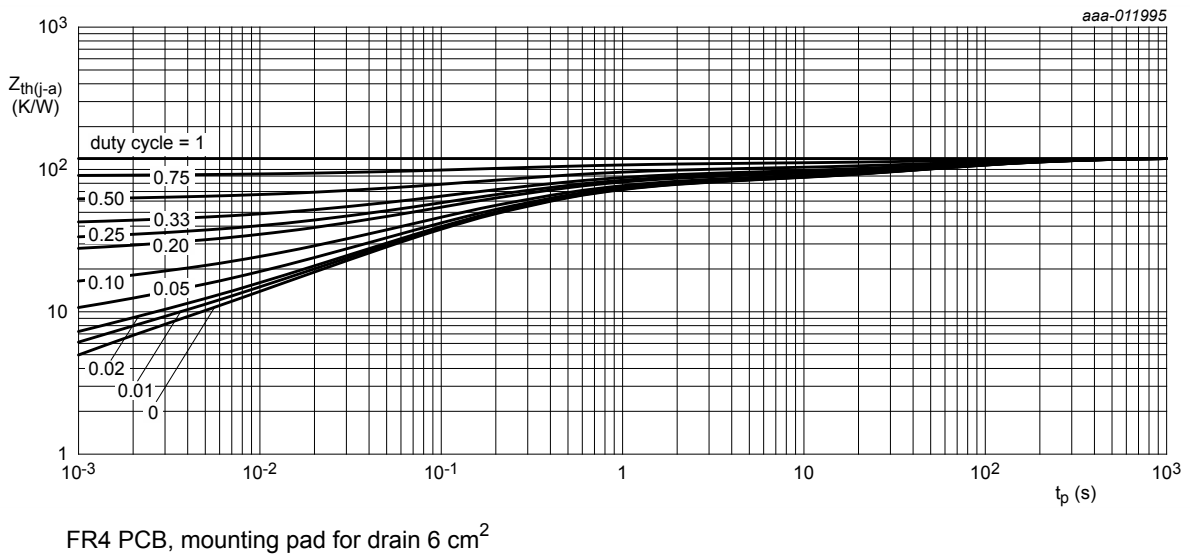


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|--|-------|------|-------|------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$ | -0.45 | -0.7 | -0.95 | V |
| I_{DSS} | drain leakage current | $V_{DS} = -20 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | - | - | -1 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | - | - | 100 | nA |
| | | $V_{GS} = -8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | - | - | -100 | nA |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 V$; $I_D = -2 A$; $T_j = 25 \text{ }^\circ C$ | - | 120 | 170 | m Ω |
| | | $V_{GS} = -4.5 V$; $I_D = -2 A$; $T_j = 150 \text{ }^\circ C$ | - | 168 | 238 | m Ω |
| | | $V_{GS} = -2.5 V$; $I_D = -1.5 A$; $T_j = 25 \text{ }^\circ C$ | - | 150 | 230 | m Ω |
| | | $V_{GS} = -1.8 V$; $I_D = -0.6 A$; $T_j = 25 \text{ }^\circ C$ | - | 200 | 320 | m Ω |
| | | $V_{GS} = -1.5 V$; $I_D = -0.1 A$; $T_j = 25 \text{ }^\circ C$ | - | 260 | 600 | m Ω |
| g_{fs} | forward transconductance | $V_{DS} = -10 V$; $I_D = -2 A$; $T_j = 25 \text{ }^\circ C$ | - | 4.5 | - | S |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $V_{DS} = -10 V$; $I_D = -2 A$; $V_{GS} = -4.5 V$; $T_j = 25 \text{ }^\circ C$ | - | 3.7 | 6.5 | nC |
| Q_{GS} | gate-source charge | | - | 0.6 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.8 | - | nC |
| C_{iss} | input capacitance | $V_{DS} = -10 V$; $f = 1 \text{ MHz}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | - | 418 | - | pF |
| C_{oss} | output capacitance | | - | 45 | - | pF |
| C_{rss} | reverse transfer capacitance | | - | 34 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = -10 V$; $I_D = -2 A$; $V_{GS} = -4.5 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 \text{ }^\circ C$ | - | 5 | - | ns |
| t_r | rise time | | - | 14 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 43 | - | ns |
| t_f | fall time | | - | 16 | - | ns |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = -0.8 A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$ | - | -0.8 | -1.2 | V |

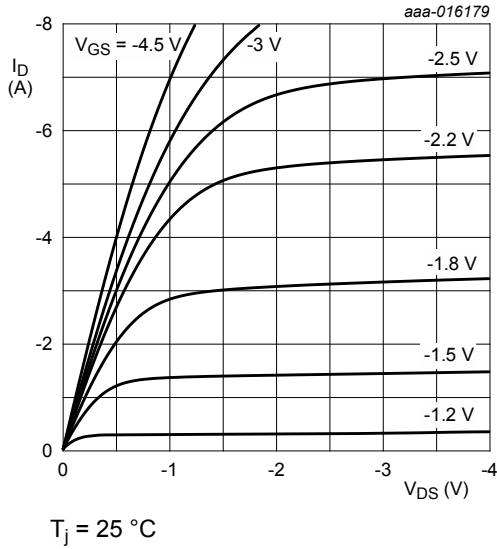


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

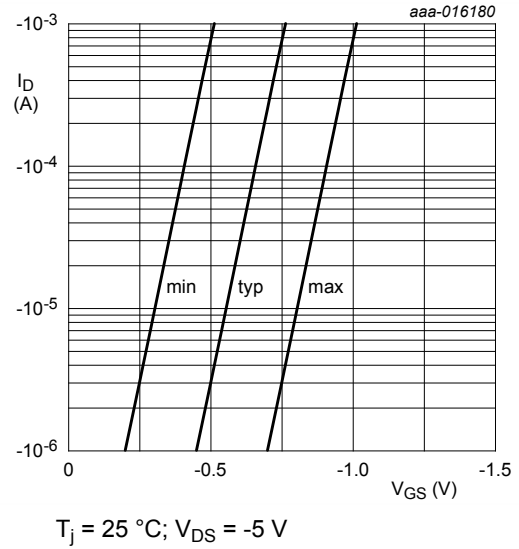


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

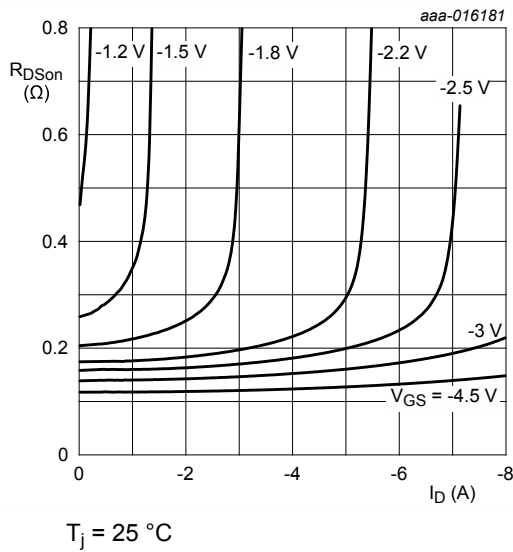


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

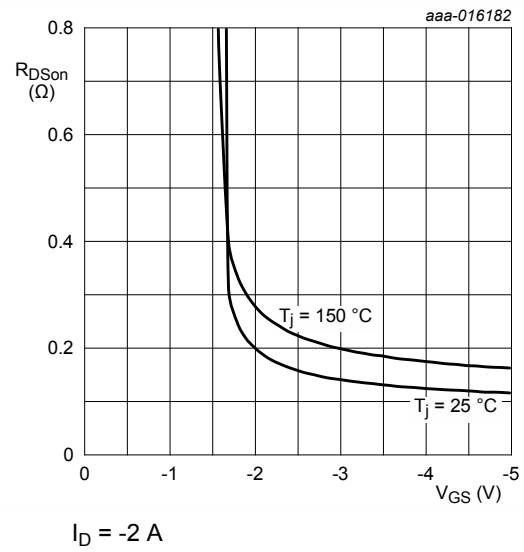
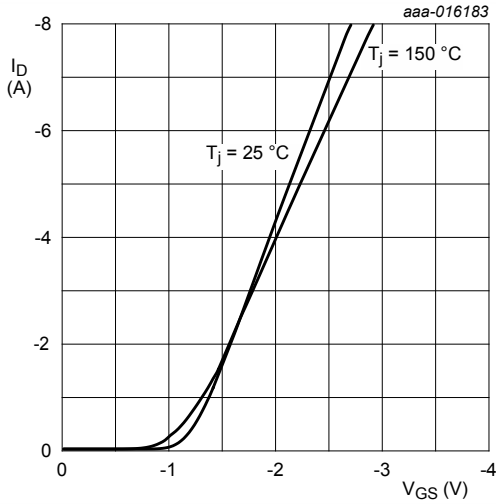


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

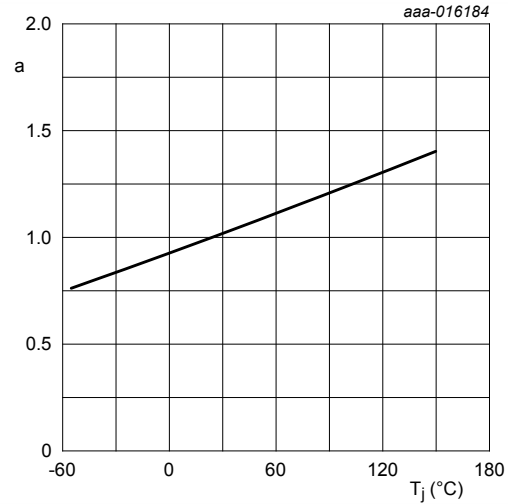
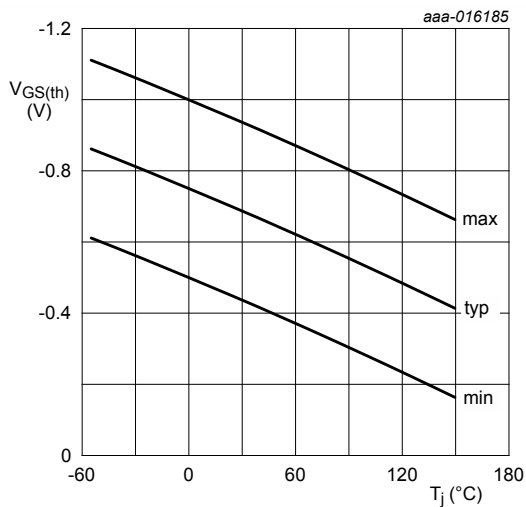


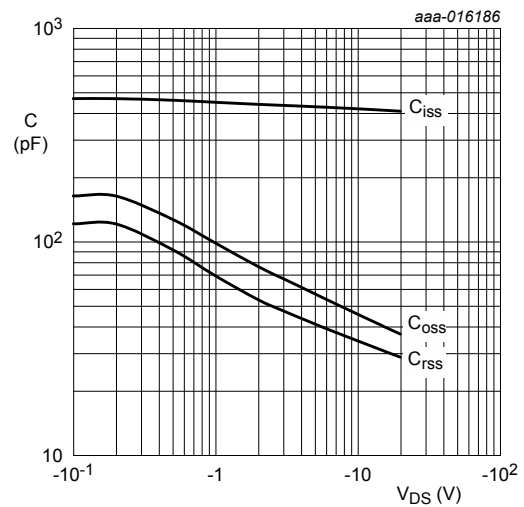
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



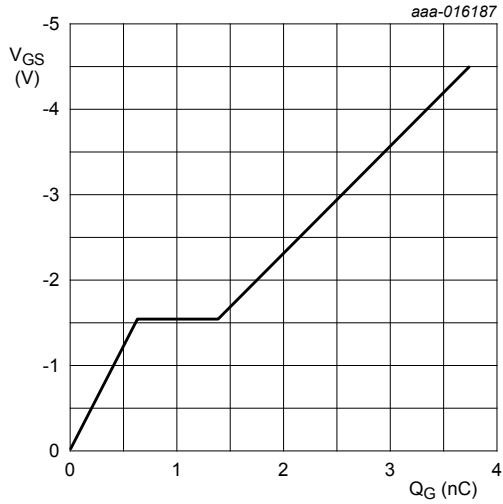
$$I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = -2 \text{ A}; V_{DS} = -10 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

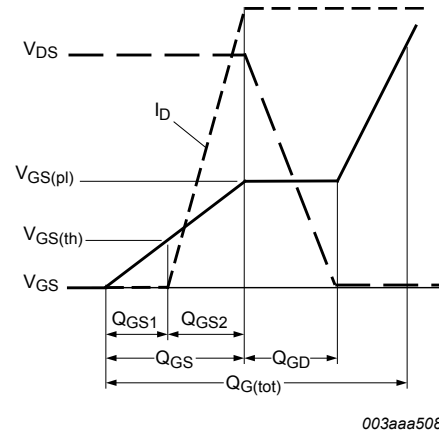
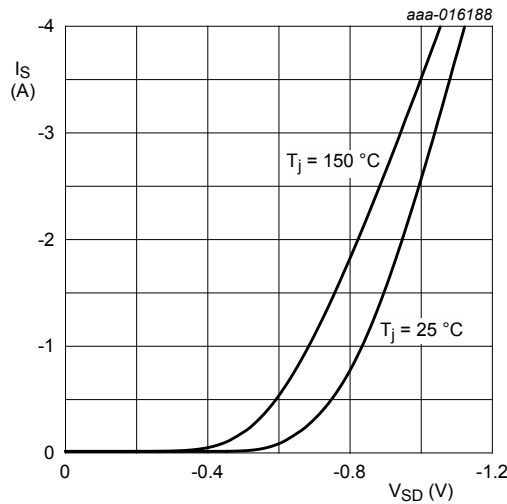


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

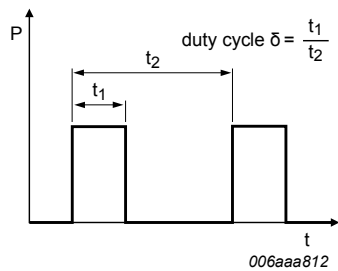


Fig. 17. Duty cycle definition

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

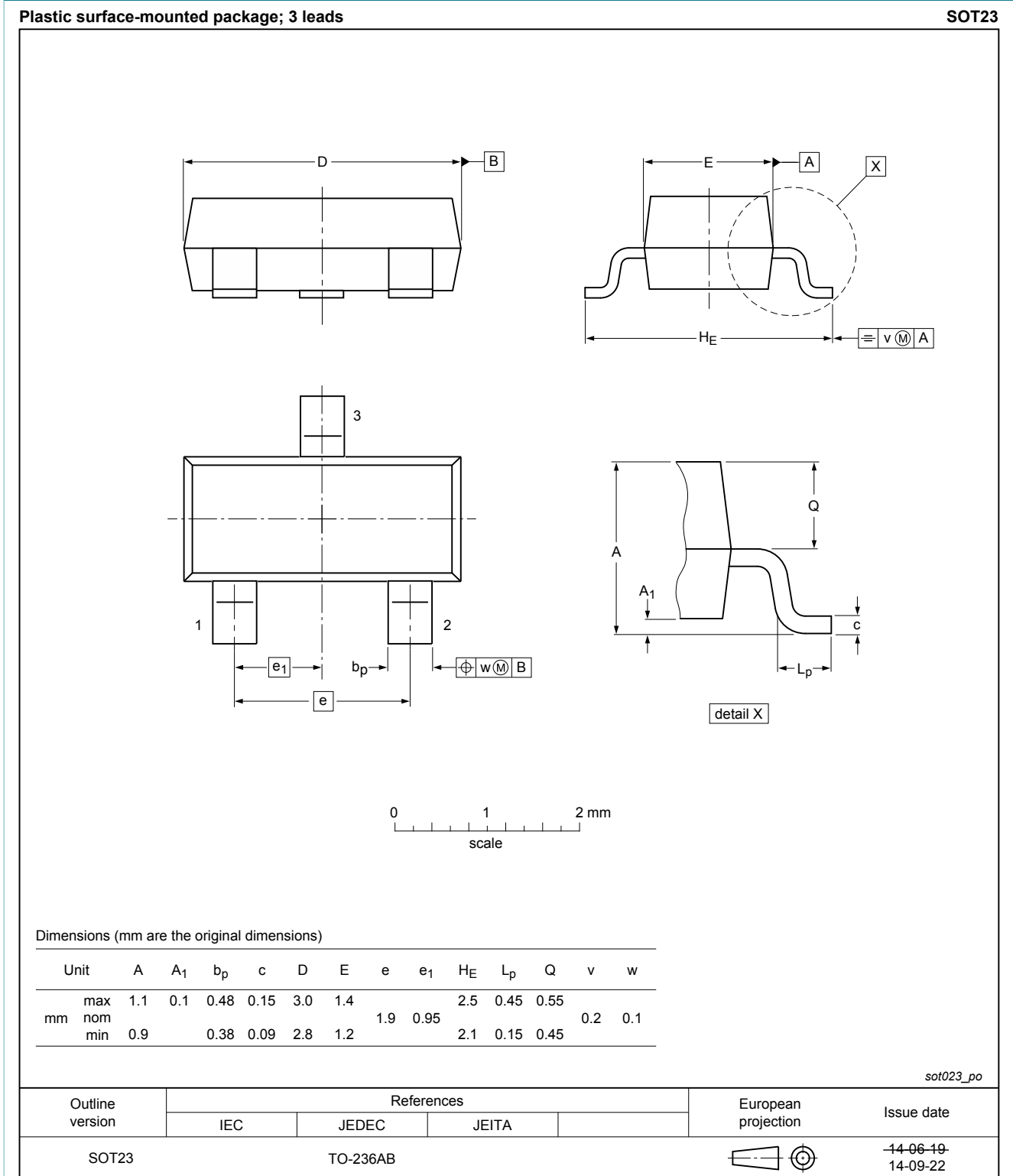


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

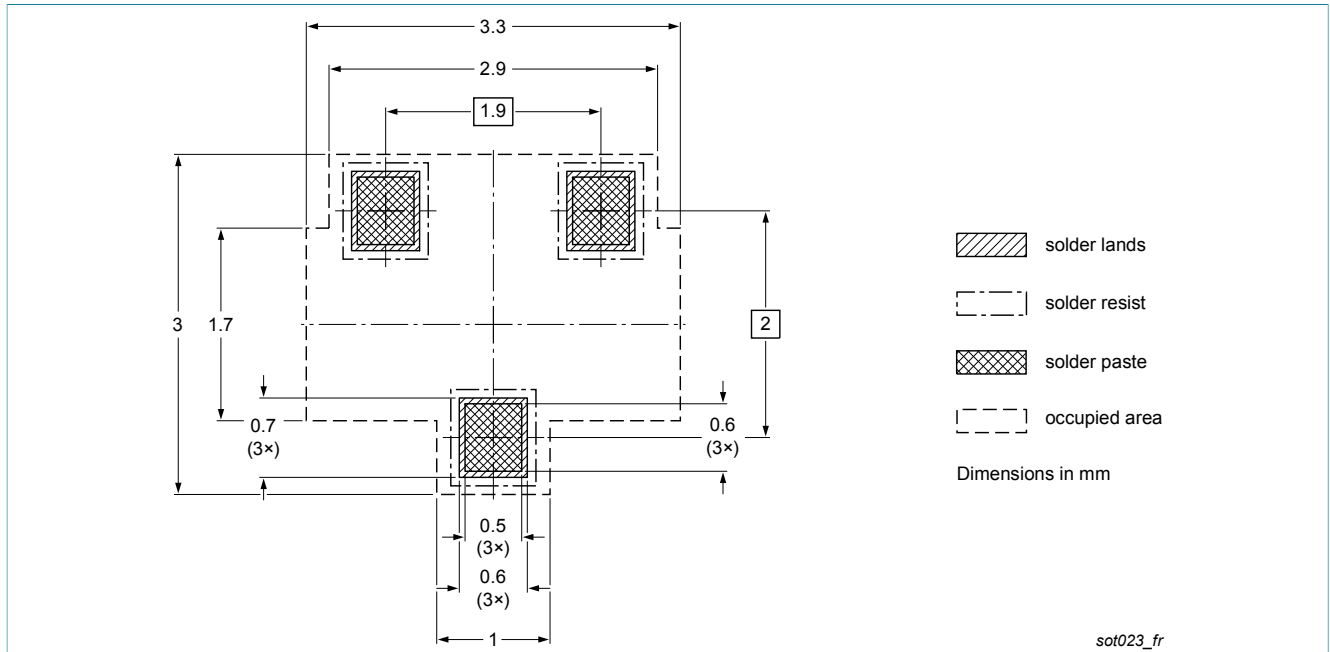


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

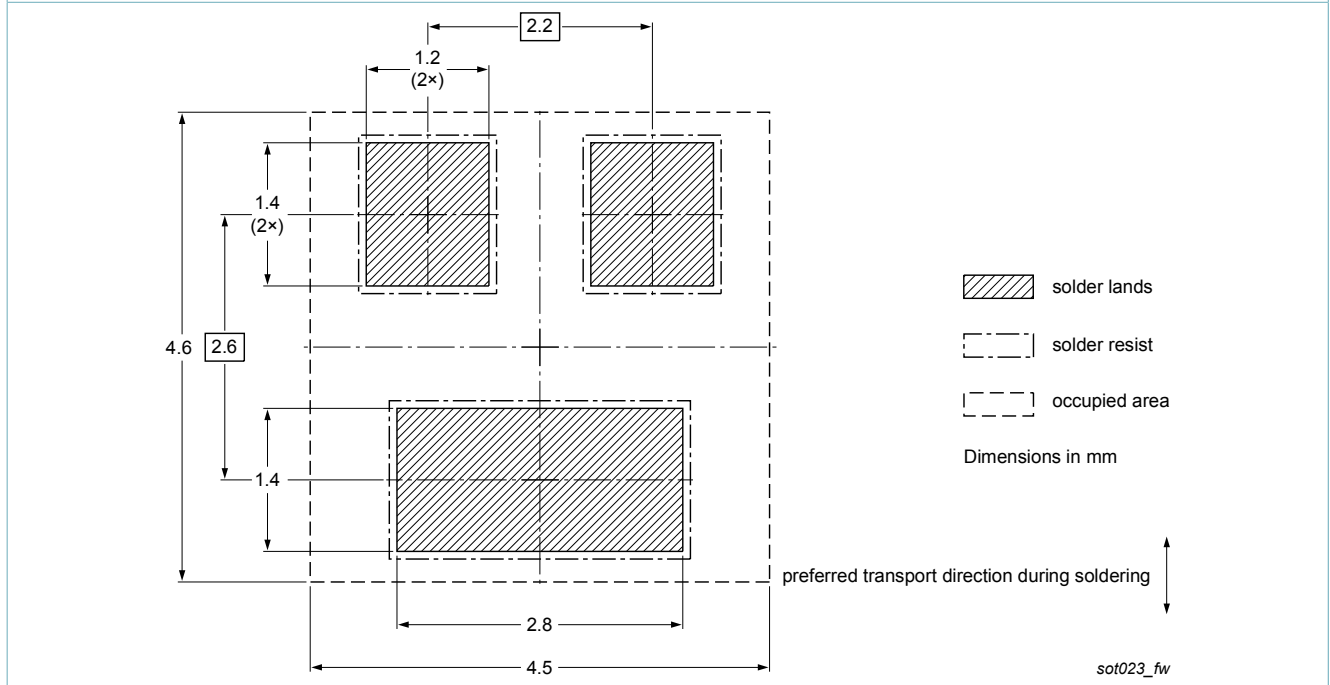


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|--------------------|---------------|--------------|
| BSH205G2 v. 2 | 20150429 | Product data sheet | - | BSH205G2 v.1 |
| Modifications: | <ul style="list-style-type: none">AEC-Q101 qualified | | | |
| BSH205G2 v.1 | 20141215 | Product data sheet | - | - |

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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